

Sheet 1 of 2

Form PTO-1449 (REV. 8-83)		US Dept. of Commerce PATENT & TRADEMARK OFFICE		ATTY DOCKET NO. 117575		APPLICATION NO. 10/689,987	
INFORMATION DISCLOSURE STATEMENT (Use several sheets if necessary)				APPLICANT Yoshikazu KASUYA			
				FILING DATE October 22, 2003			
U.S. PATENT DOCUMENTS							
EXAMINER INITIAL		DOCUMENT NUMBER	DATE	NAME	CLASS	SUB CLASS	
CAL	1	6,255,166 B1	07/03/2001	Ogura et al.			
	2	5,408,115	04/18/1995	Chang			
	3	5,969,383	10/19/1999	Chang et al.			
	4	5,422,504	06/06/1995	Chang et al.			
	5	5,494,838	02/27/1996	Chang et al.			
	6	6,177,318 B1	01/23/2001	Ogura et al.			
	7	6,248,633 B1	06/19/2001	Ogura et al.			
	8	US 2002-0100929	08/01/2002	Ebina et al.			
	9	US 2002-0127805	09/12/2002	Ebina et al.			
	10	6,413,821	07/02/2002	Ebina et al.			
	11	6,518,124	02/11/2003	Ebina et al.			
	12	US 2003-0054610	05/20/2003	Ebina et al.			
	13	US 2003-0057505	03/27/2003	Ebina et al.			
	14	US 2003-0058705	03/27/2003	Ebina et al.			
	15	US 2003-0060011	03/27/2003	Ebina et al.			
	16	US 2003-0190805	10/09/2003	Inoue			
	17	US 2003-0186505	10/02/2003	Shibata			
	18	US 2003-0166321	09/04/2003	Kasuya			
	19	US 2003-0157767	08/21/2003	Kasuya			
	20	US 2003-0166322	09/04/2003	Kasuya			
	21	US 2003-0166320	09/04/2003	Kasuya			
	22	US 2003-0211691	11/13/2003	Ueda			
	23	10/636,562 ✓	08/08/2003	Inoue			
	24	10/636,581 ✓	08/08/2003	Yamamukai			
	25	10/636,582 ✓	08/08/2003	Inoue			
	26	10/614,985 ✓	07/09/2003	Inoue			
	27	10/689,993 ✓	10/22/2003	Kasuya			
	28	10/690,025	10/22/2003	Kasuya			

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Sheet 2 of 2

29	10/689,990	10/22/2003	Kasuya		
FOREIGN PATENT DOCUMENTS					
	DOCUMENT NUMBER	DATE	COUNTRY	CLASS	SUB CLASS
CAL	30	JP A 2001-156188 (with abstract and translation)	06/08/2001	Japan	
CAL	31	JP A 7-161851 (with abstract and translation)	06/23/1995	Japan	
CAL	32	JP B1 2978477 (with translation)	09/10/1999	Japan	
OTHER DOCUMENTS (Including Author, Title, Date, Pertinent Pages, etc.)					
CAL	33	Hayashi et al. "Twin MONOS Cell with Dual Control Gates", 2000 Symposium on VLSI Technology Digest of Technical Papers			
CAL	34	Chang et al. "A New SONOS Memory Using Source-Side Injection for Programming", IEEE Electron Device Letters, Vol. 19, No. 7, July 1998, pp 253-255			
CAL	35	Chen et al. "A Novel Flash Memory Device with S Plit Gate Source Side Injection and ONO Charge Storage Stack (SPIN), 1997 Symposium on VLSI Technology Digest of Technical Papers, pp 63-64			

EXAMINER				DATE CONSIDERED	
C. J. [Signature]				6/10/05	
Examiner: Initial if citation considered, whether or not citation is in conformance with M.P.E.P. 609; draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.					

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